

## **Supporting Information**

### **Degradation Analysis of Triple Cation Perovskite Solar Cells by Electrochemical Impedance Spectroscopy**

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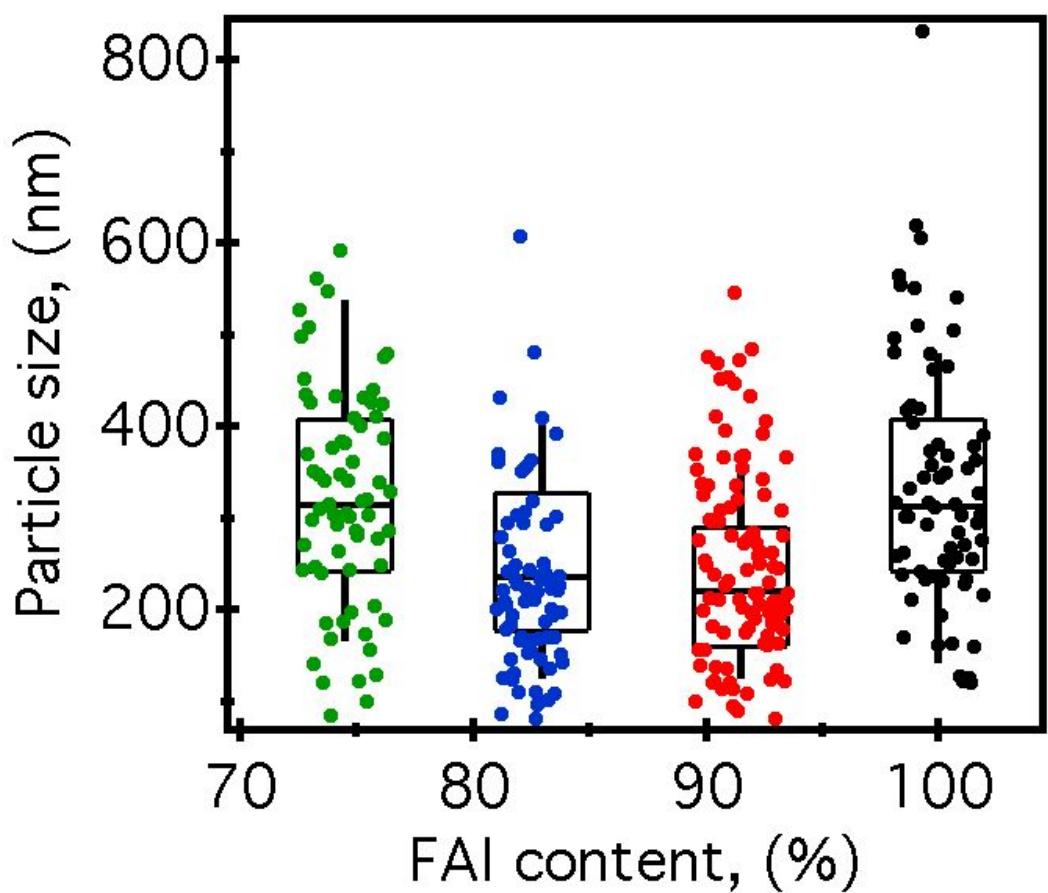
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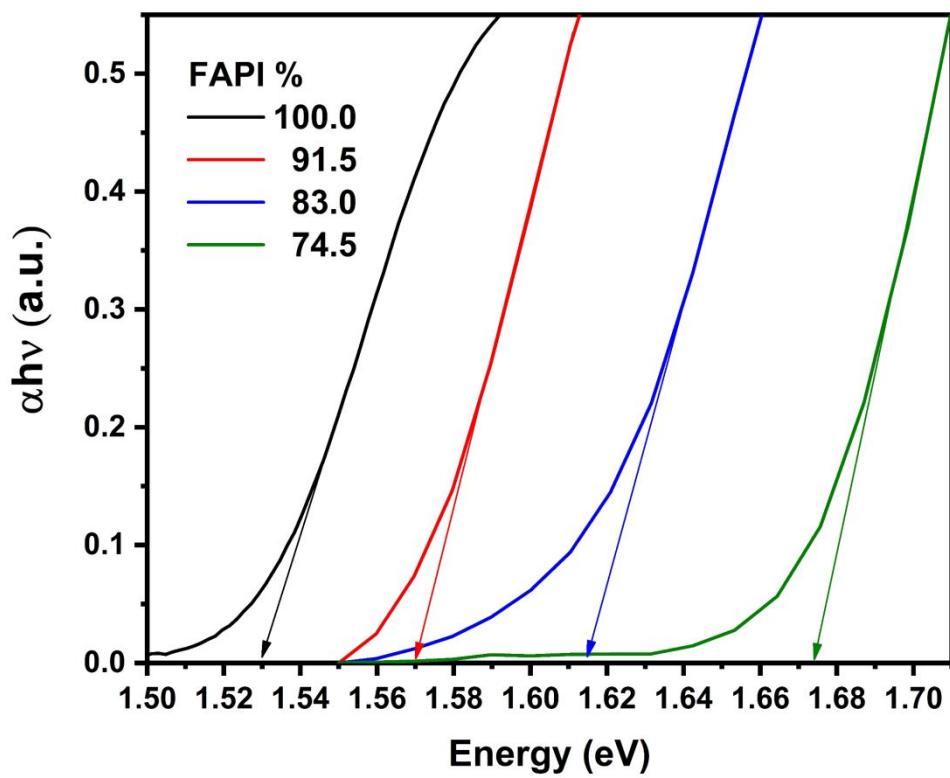
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**Figure S1.** The mean diameter and the standard deviation of the grain size distribution as a function of FAPI content.



**Figure S2.** Tauc plot of the different perovskite thin film concentrations.

**Table S1.** Shows the statistical values of the photovoltaic parameters of 15 samples for each FAPI concentration.

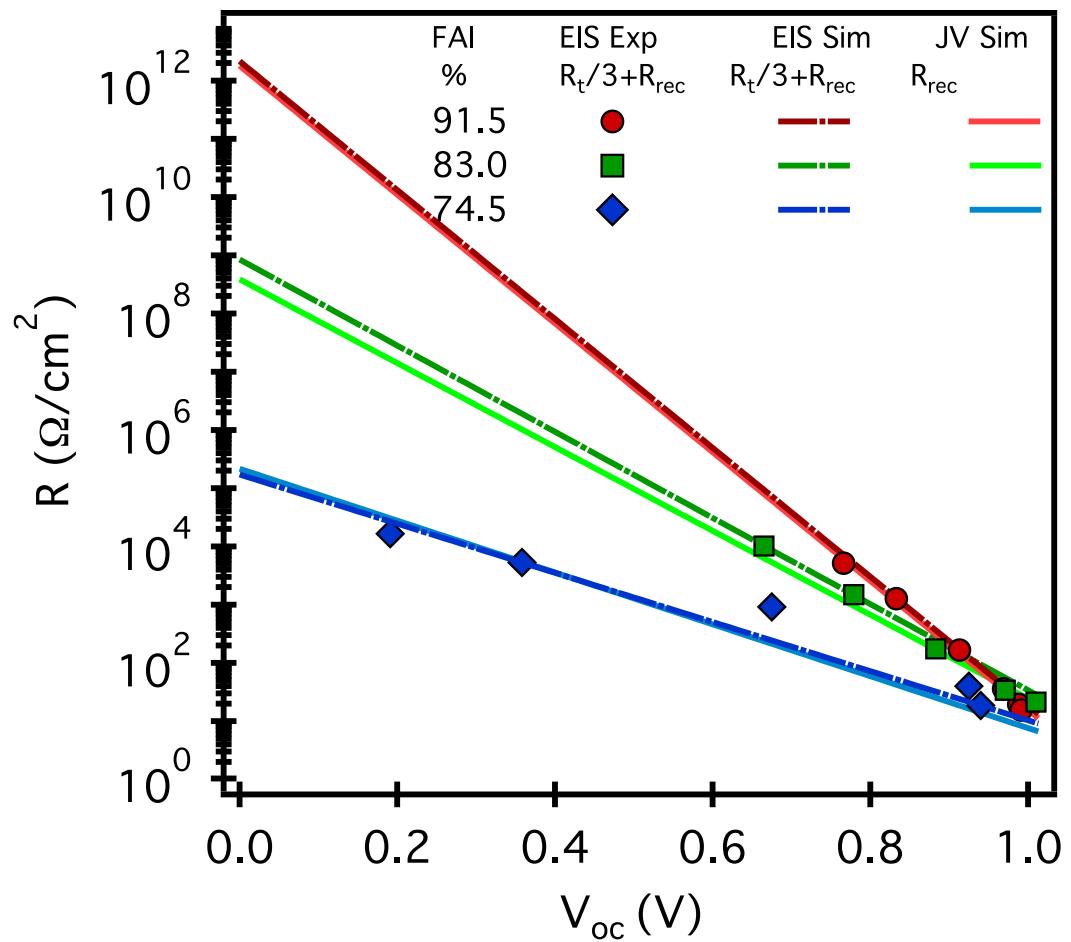
FAI %		J <sub>sc</sub> (mA/cm <sup>2</sup> )	V <sub>oc</sub> (V)	FF (%)	η (%)
100	Best	22.3	0.965	75.5	16.1
	Mean	21.2±0.6	0.941±0.012	72.8±4.1	14.7±0.7
91.50	Best	21.0	1.044	80.6	17.7
	Mean	21.0±0.2	1.012±0.019	76.3±2.4	16.2±0.6
83	Best	20.1	1.124	78.9	18.55
	Mean	20.6±0.3	1.108±0.024	77.0±1.5	17.6±0.7
74.50	Best	18.45	1.158	79.7	17.0
	Mean	18.1±0.5	1.134±0.028	73.8±5.5	15.1±1.2

**Table S2.** Increase of band gap and V<sub>oc</sub> for fresh samples.

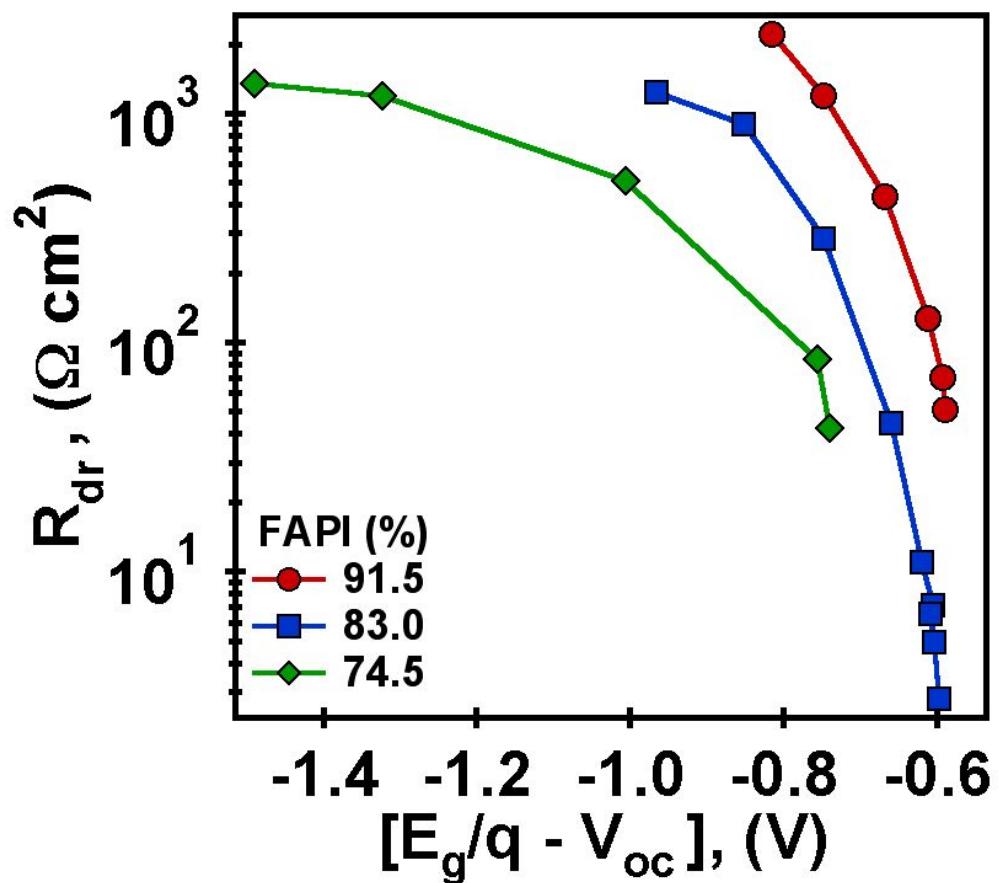
F API %	E <sub>g</sub> /q (V)	V <sub>oc</sub> (V)	Δ E <sub>g</sub> /q (V)	Δ Average V <sub>oc</sub> (V)
100	1.53	0.941	0	0
91.50	1.58	1.012	0.05	0.071
83	1.63	1.108	0.1	0.167
74.50	1.68	1.134	0.15	0.193

**Table S3.** Photovoltaic parameters of the PCSs after 90 days from device fabrication.

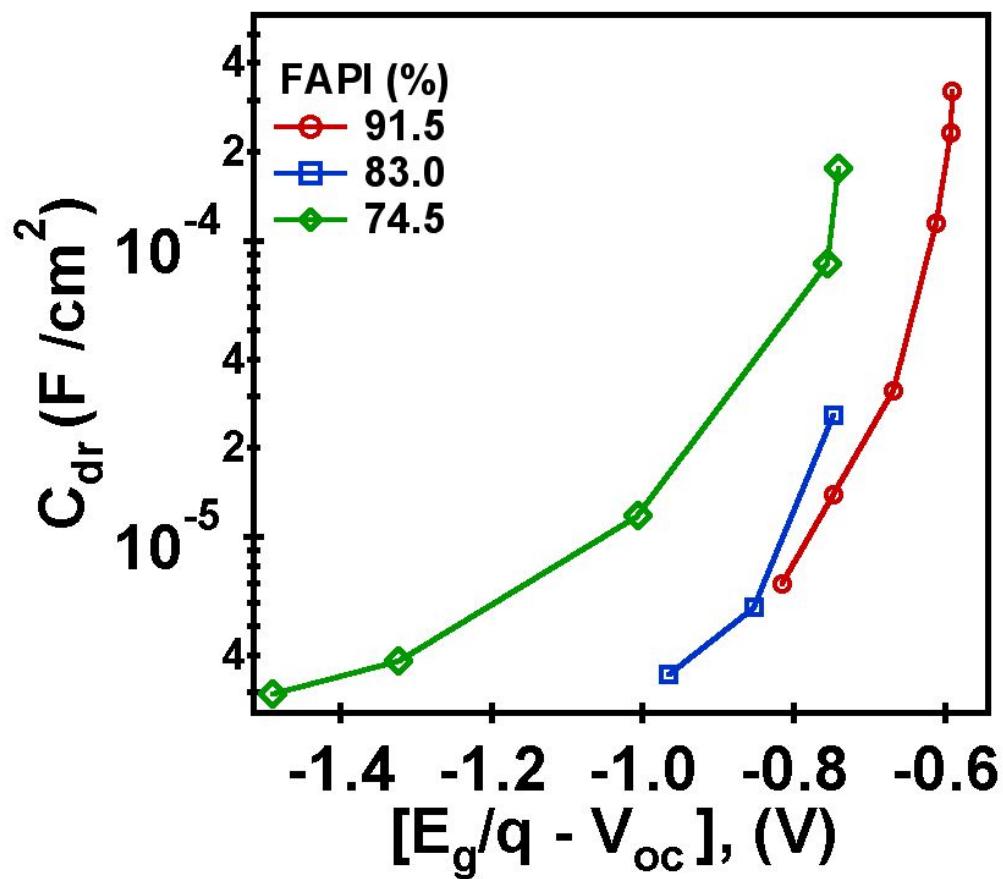
F API %		J <sub>sc</sub> mA/cm <sup>2</sup>	V <sub>oc</sub> V	FF %	η %
100	Best	NA	NA	NA	NA
	Mean	NA	NA	NA	NA
91.50	Best	20.6	1.084	62.5	14.0
	Mean	19.3±1.2	1.079±0.014	56.7±8.7	11.8±2.1
83	Best	18.9	1.113	57.7	12.1
	Mean	17.7±1.6	1.075±0.036	52.8±3.2	10.0±1.3
74.50	Best	18.56	1.016	61.16	11.54
	Mean	15.6±2.5	1.037±0.026	61.7±2.3	10.0±1.5



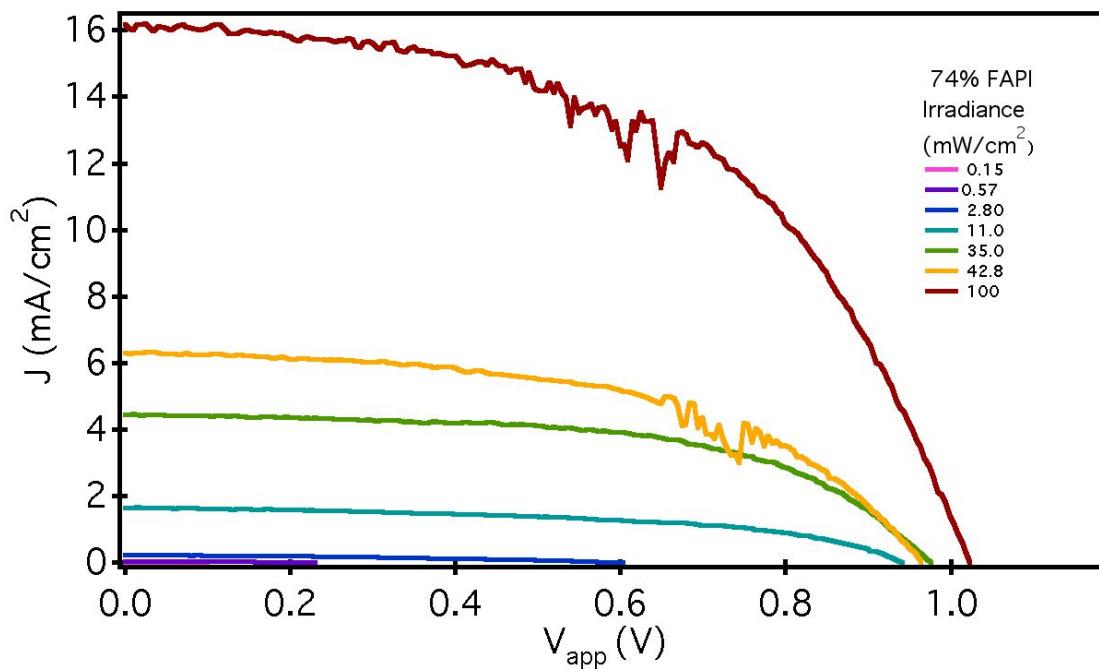
**Figure S3.** Resistivity vs open circuit voltage of the three different PVSKs.



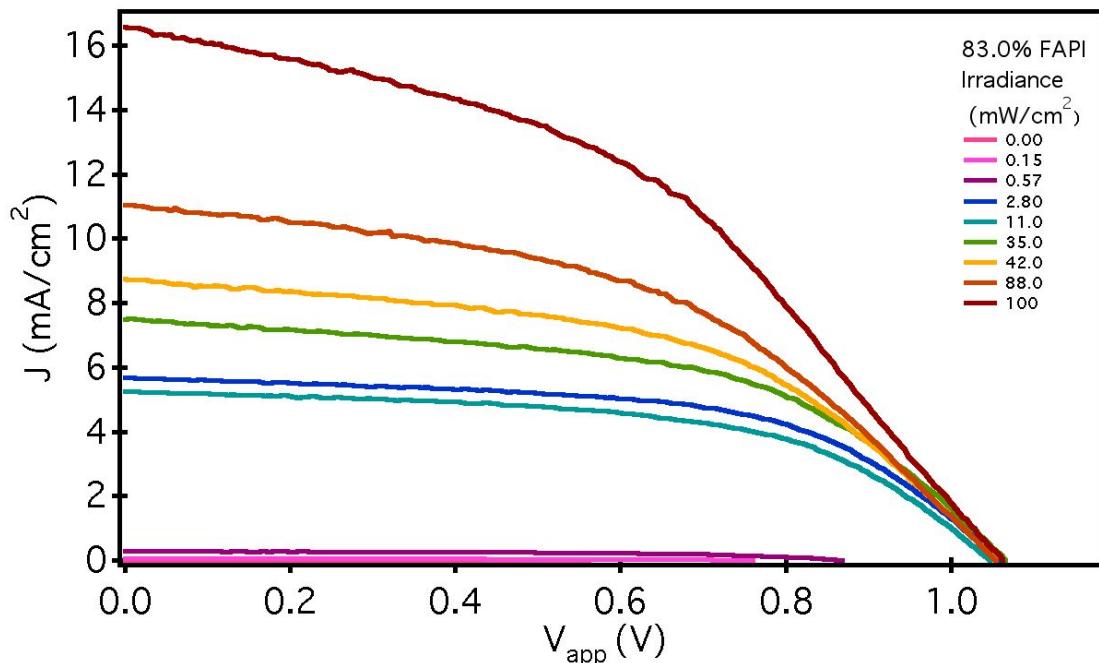
**Figure S4.** Dielectric relaxation resistance vs open circuit voltage corrected by the optical band gap for three different PVSks.



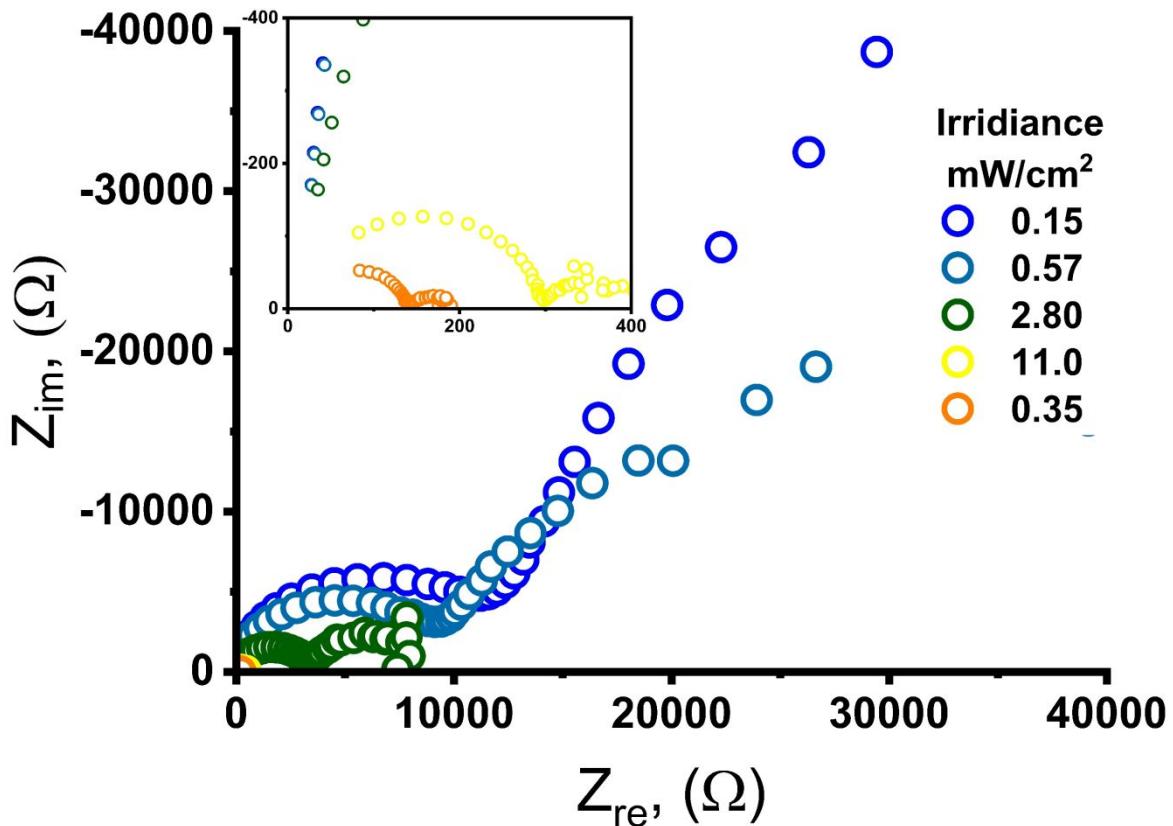
**Figure S5.** Dielectric relaxation capacitance vs open circuit voltage corrected by the optical band gap for three different PVSKs.



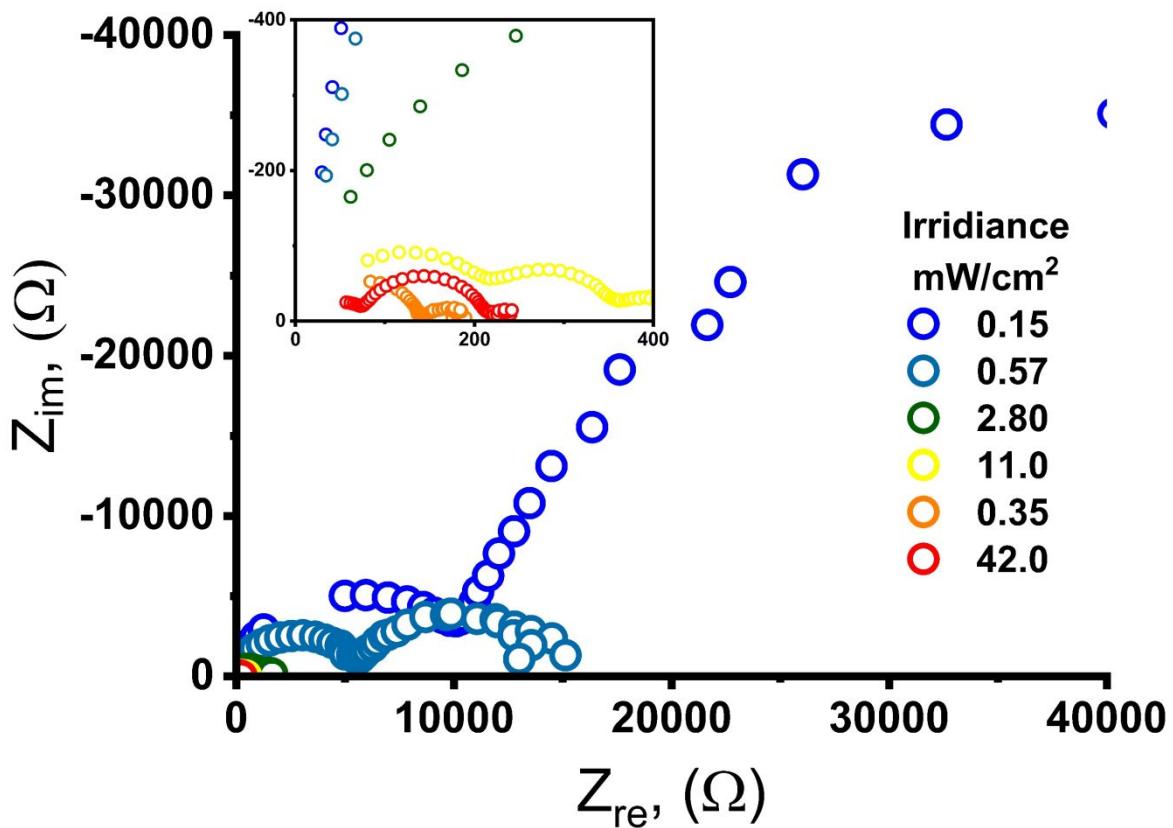
**Figure S6.** J-V curves of the PSC with 74.5% of FAPI at several irradiances.



**Figure S7.** J-V curves of the PSC with 83% of FAPI at several irradiances. S-8



**Figure S8.** Nyquist plot of the impedances for the sample with 74.5% of FAPI measured under open circuit conditions at several irradiances.



**Figure S9.** Nyquist plot of the impedances for the sample with 83% of FAPI measured under open circuit conditions at several irradiances.